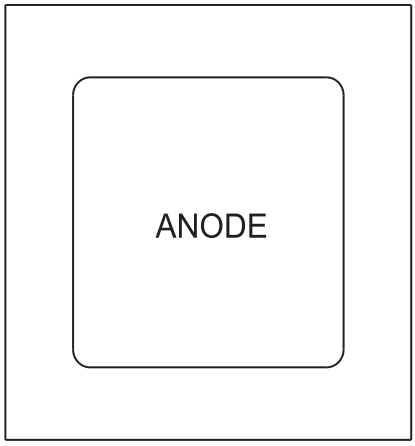
# PROCESS CPZ19
## Zener Diode
### 0.5 Watt Zener Diode Chip

**PROCESS DETAILS**

| | |
|---|---|
| Process | EPITAXIAL PLANAR |
| Die Size | 17.7 x 17.7 MILS |
| Die Thickness | 7.5 MILS |
| Anode Bonding Pad Area | 11 x 11 MILS |
| Top Side Metalization | Al - 13,000Å |
| Back Side Metalization | Au - 14,000Å |

**GEOMETRY**




BACKSIDE CATHODE

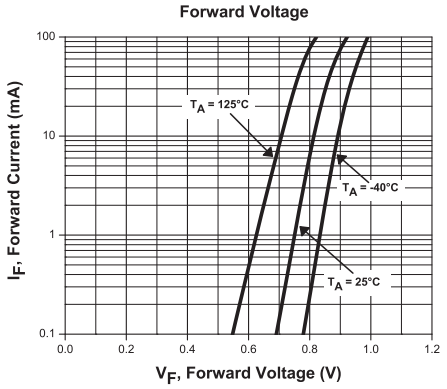
R0

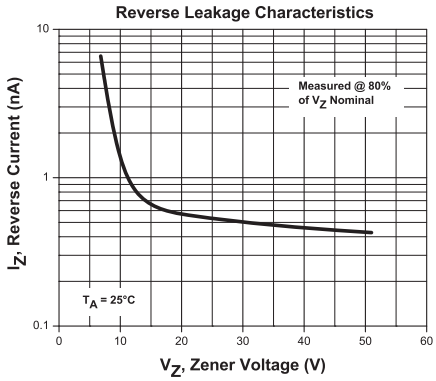
**GROSS DIE PER 4 INCH WAFER**
36,642

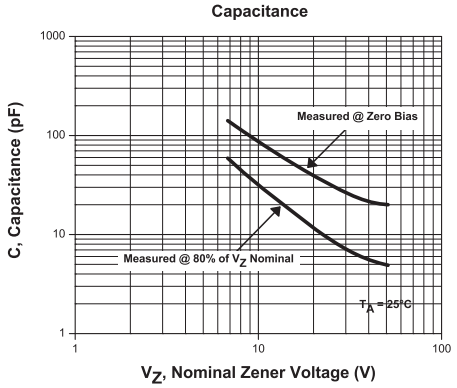
**PRINCIPAL DEVICE TYPES**
CMPZ5235B
THRU
CMPZ5261B

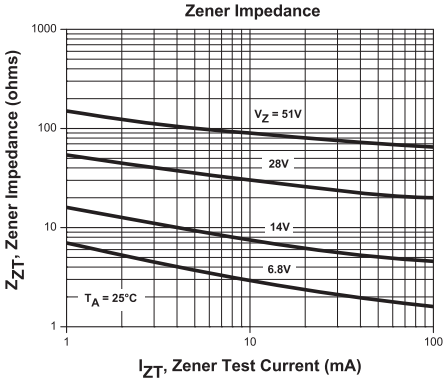
# PROCESS CPZ19

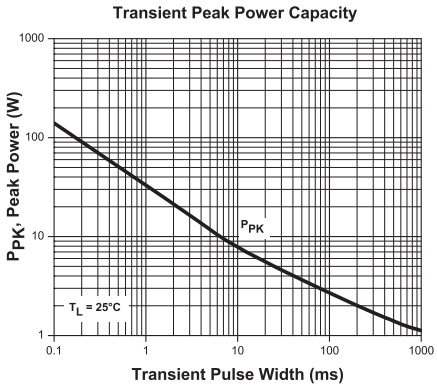
## Typical Electrical Characteristics

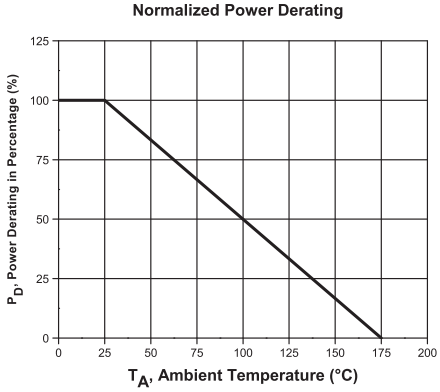



R5 (22-March 2010)